Page 1, first and second full paragraphs (lines 2-11), replace the paragraphs with:

The present invention relates to a semiconductor

manufacturing technique and more particularly to a technique

useful in its application to the improvement in the quality of

a semiconductor device.

As examples of semiconductor devices having a semiconductor chip with a semiconductor integrated circuit formed thereon, further having bump electrodes (e.g., solder balls) as external terminals and a wiring board which supports the semiconductor chip, there are known CSPs (Chip Scale Packages) or BGAs (Ball Grid Arrays).

Pages 1 and 2, the paragraph bridging these pages from page 1, line 22 to page 2, line 6, replace the paragraph with:

According to the block molding method, a multi device substrate is used on which plural device areas corresponding to thin film wiring boards are formed in a partitioned and contiguous manner and are sealed with resin by molding while being covered together. After the sealing with resin, dicing is performed for division (formation of individual pieces) into each device area.

Page 2, first full paragraph (lines 7-11), replace the paragraph with:

This semiconductor device manufacturing method using such a block molding method, as well as the structure of the semiconductor device are disclosed, for example, in Japanese Unexamined Patent Publication No. 2000-124163 or Hei 11(1999)-214588.

Page 2, third full paragraph (lines 19-25), replace the paragraph with:

As described in the above publication, the case where an internal stress is created due to a difference in thermal expansion coefficient between the substrate and the molding resin is based on the premise that the strength of the substrate is so high as to generate a force resistive to a relative deformation (difference in volume change) between the molding resin and the substrate.

Page 3, second full paragraph (lines 9-15), replace the paragraph with:

Thus, the molding resin and the substrate give rise to a relative deformation due to a difference in thermal expansion coefficient or shrinkage of the resin on curing. However, by